# 2SD1198, 2SD1198A

### Silicon NPN epitaxial planer type darlington

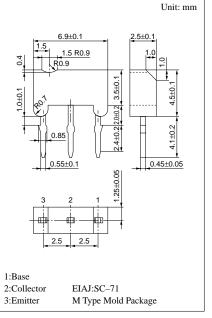
#### For low-frequency amplification

#### Features

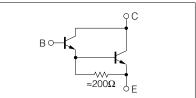
- Forward current transfer ratio h<sub>FE</sub> is designed high, which is appropriate to the driver circuit of motors and printer bammer: h<sub>FE</sub> = 4000 to 40000.
- A shunt resistor is omitted from the driver.
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

Parameter		Symbol	Ratings	Unit		
Collector to	2SD1198	V	30	v		
base voltage	2SD1198A	V <sub>CBO</sub>	60	v		
Collector to	2SD1198	V	25	v		
emitter voltage	2SD1198A	V <sub>CEO</sub>	50	v		
Emitter to base voltage		$V_{EBO}$	5	V		
Peak collector current		I <sub>CP</sub>	1.5	А		
Collector current		$I_C$	1	А		
Collector power dissipation		$P_{C}^{*}$	1	W		
Junction temperature		Tj	150	°C		
Storage temperature		T <sub>stg</sub>	-55 ~ +150	°C		

#### Absolute Maximum Ratings (Ta=25°C)



#### Internal Connection



\* Printed circuit board: Copper foil area of 1cm<sup>2</sup> or more, and the board thickness of 1.7mm for the collector portion

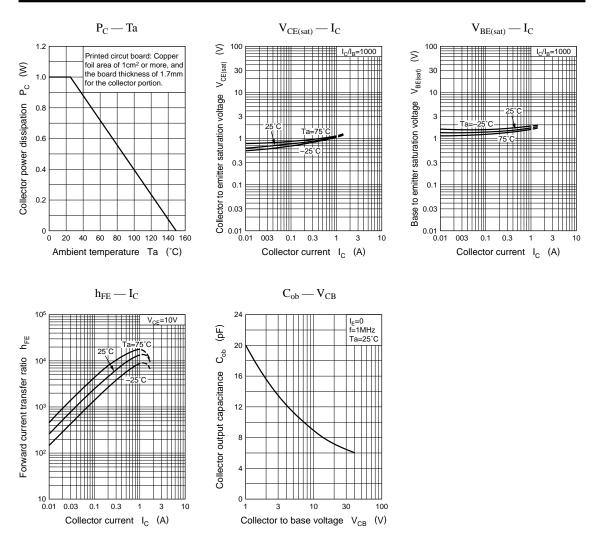
#### Electrical Characteristics (Ta=25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff	2SD1198	т	$V_{CB} = 25V, I_E = 0$			100	
current	2SD1198A	I <sub>CBO</sub>	$V_{CB} = 45V, I_E = 0$			100	nA
Emitter cutoff curren	t	I <sub>EBO</sub>	$V_{EB} = 4V, I_{C} = 0$			100	nA
Collector to base	2SD1198	V	$I_{\rm C} = 100 \mu A, I_{\rm B} = 0$	30			- v
voltage	2SD1198A	V <sub>CBO</sub>		60			
Collector to emitter	2SD1198	V	$I_{\rm C} = 1 {\rm mA},  I_{\rm B} = 0$	25			v
voltage	2SD1198A	V <sub>CEO</sub>		50			
Emitter to base voltage V <sub>EB0</sub>		V <sub>EBO</sub>	$I_E = 100 \mu A, I_C = 0$	5			V
Forward current transfer ratio h		${h_{FE}}^{*1}$	$V_{CE} = 10V, I_C = 1A^{*2}$	4000		40000	
Collector to emitter saturation voltage $V_{CE(s)}$		V <sub>CE(sat)</sub>	$I_{\rm C} = 1$ A, $I_{\rm B} = 1$ mA <sup>*2</sup>			1.8	V
Base to emitter saturation voltage V		V <sub>BE(sat)</sub>	$I_{C} = 1A, I_{B} = 1mA^{*2}$			2.2	V
Transition frequency		f <sub>T</sub>	$V_{CB} = 10V, I_E = -50mA, f = 200MHz$		150		MHz

<sup>\*1</sup>h<sub>FE</sub> Rank classification

Rank	Q	R	S	
$\mathbf{h}_{\mathrm{FE}}$	$4000 \sim 10000$	8000 ~ 20000	16000 ~ 40000	

\*2 Pulse measurement



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